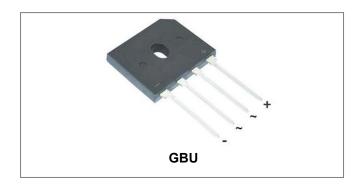






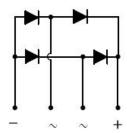
# GBU6005 THRU GBU610 Single-Phase 6.0A Glass Passivated Bridge Rectifier



#### **Features**

- Glass passivated die construction
- Low forward voltage drop
- High current capability
- High surge current capability
- Plastic material-UL flammability 94V-0
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

## **Circuit Diagram**



#### **Mechanical Data**

- Case: GBU, Molded plastic
- Terminals: Plated leads solderable per MIL-STD-202, Method 208
- Polarity: as marked on case
- Mounting Position: Any
- Lead Free: For RoHS / Lead Free Version

#### Maximum Ratings:@T<sub>A</sub>=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Type Number	Symbol	GBU 6005	GBU 601	GBU 602	GBU 604	GBU 606	GBU 608	GBU 610	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>DC</sub>	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V <sub>RMS</sub>	35	70	140	280	420	560	700	V
Average forward rectified output current (Note 1) @T <sub>A</sub> = 40°C	lo	6.0						Α	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	120						А	

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#### Electrical Characteristics:@TA=25°C unless otherwise specified

Type Number	Symbol	GBU 6005	GBU 601	GBU 602	GBU 604	GBU 606	GBU 608	GBU 610	Units
Forward Voltage (per element) @I <sub>F</sub> =3A @I <sub>F</sub> =6A	V <sub>F</sub>	1.0 1.1			V				
Peak Reverse Current @T <sub>A</sub> = 25°C At Rated DC Blocking Voltage @T <sub>A</sub> = 125°C	I <sub>RM</sub>				5.0 500				μA
Typical Junction Capacitance(per leg) (Note 2)	C₃	65						pF	

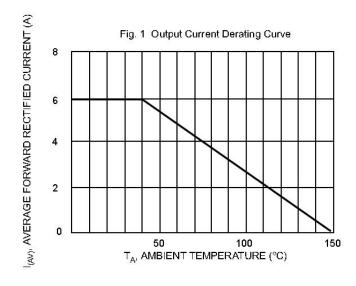
<sup>\*</sup> Pulse width < 300  $\mu$ s, duty cycle < 2%

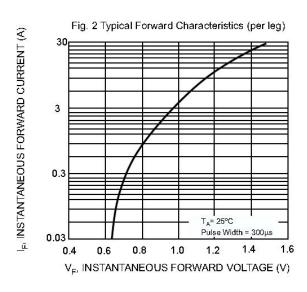
## Thermal-Mechanical Specifications:@T<sub>A</sub>=25°C unless otherwise specified

Type Number	Symbol	GBU 6005	GBU 601	GBU 602	GBU 604	GBU 606	GBU 608	GBU 610	Units
Typical Thermal Resistance (per leg) $\begin{array}{c c} R_{\text{BJA}} & 20 \\ R_{\text{BJL}} & 2.2 \end{array}$					°C/W				
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150							°C

Note: 1. Mounted on glass epoxy PC board with 1.3mm² solder pad. 2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

### **Ratings and Characteristics Curves**



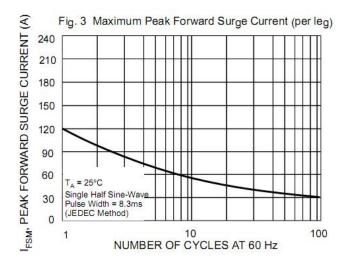


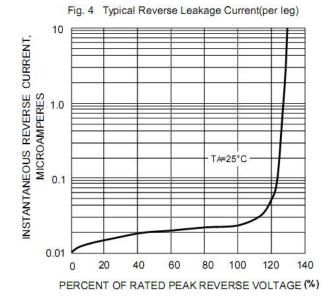
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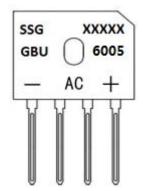


## **Ordering Information**

Device	Package	Plating	Shipping
GBU6005 THRU GBU610	GBU(Pb-Free)	Pure Sn	20pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

## **Marking Diagram**



Where XXXXX is YYWWL

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

 GBU6005
 = Type Number

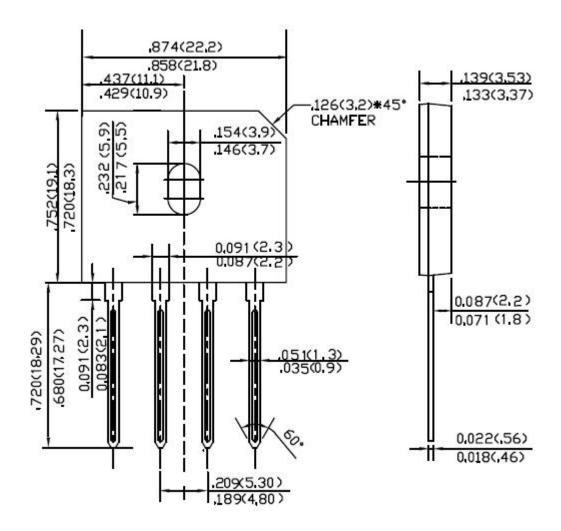
Cautions: Molding resin Epoxy resin UL:94V-0







## **Mechanical Dimensions GBU (Inches/Millimeters)**



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